Masakazu Aono

List of Articles by Year
in descending order

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248 peer-reviewed articles	16,433 peer-reviewed citations	31060 54 peer-reviewed h-index	360111 4.42 score
291 documents	19834 doc citations	26244 61 h-index	22706 citing authors

#	Article	IF	Citations
1	Quantum Conductance in Memristive Devices: Fundamentals, Developments, and Applications. Advanced Materials, 2022, 34, .	17.5	91
2	Single-molecule detection with enhanced Raman scattering of tungsten oxide nanostructure. Nanoscale, 2022, 14, 14552-14557.	3.6	3
3	Impact of moisture absorption on the resistive switching characteristics of a polyethylene oxide-based atomic switch. Journal of Materials Chemistry C, 2021, 9, 11198-11206.	3.6	10
4	Significant roles of the polymer matrix in the resistive switching behavior of polymer-based atomic switches. Journal Physics D: Applied Physics, 2019, 52, 445301.	2.2	19
5	Dark-Field Scattering and Local SERS Mapping from Plasmonic Aluminum Bowtie Antenna Array. Micromachines, 2019, 10, 468.	2.0	9
6	Tunable Magnetism of Organometallic Nanoclusters by Graphene Oxide On-Surface Chemistry. Scientific Reports, 2019, 9, .	2.7	7
7	Morphological Change of Molecular Assemblies through On-Surface Chemical Reaction. Journal of Physical Chemistry C, 2019, 123, 29679-29685.	2.3	6
8	Reversible manipulation of lattice defects in single-crystal SnO2 microrod by applying mechanical stress and voltage. Journal of Applied Physics, 2019, 125, .	1.6	3
9	Nanoarchitectonics for Controlling the Number of Dopant Atoms in Solid Electrolyte Nanodots. Advanced Materials, 2018, 30, .	17.5	83
10	Oxygen vacancy drift controlled three-terminal ReRAM with a reduction in operating gate bias and gate leakage current. Solid State Ionics, 2018, 328, 30-34.	2.6	6
11	Ionic decision-maker created as novel, solid-state devices. Science Advances, 2018, 4, .	8.1	32
12	Thermally stable resistive switching of a polyvinyl alcohol-based atomic switch. Journal of Materials Chemistry C, 2018, 6, 6460-6464.	3.6	46
13	Self-Sensitization and Photo-Polymerization of Diacetylene Molecules Self-Assembled on a Hexagonal-Boron Nitride Nanosheet. Polymers, 2018, 10, 206.	3.4	10
14	Highly Reproducible and Regulated Conductance Quantization in a Polymer-Based Atomic Switch. Advanced Functional Materials, 2017, 27, .	11.9	86
15	Operating mechanism and resistive switching characteristics of two- and three-terminal atomic switches using a thin metal oxide layer. Journal of Electroceramics, 2017, 39, 143-156.	1.3	32
16	Quantum transport localization through graphene. Nanotechnology, 2017, 28, 035703.	1.9	5
17	Ultrahigh-density data storage into thin films of fullerene molecules. Japanese Journal of Applied Physics, 2016, 55, 1102B4.	1.2	12
18	Kinetic factors determining conducting filament formation in solid polymer electrolyte based planar devices. Nanoscale, 2016, 8, 13976-13984.	3.6	51

#	Article	IF	Citations
19	Nanoionic devices enabling a multitude of new features. Nanoscale, 2016, 8, 13873-13879.	3.6	33
20	Nanoionic devices: Interface nanoarchitechtonics for physical property tuning and enhancement. Japanese Journal of Applied Physics, 2016, 55, 1102A4.	1.2	28
21	Multiple-probe scanning probe microscopes for nanoarchitectonic materials science. Japanese Journal of Applied Physics, 2016, 55, 1102A7.	1.2	12
22	Self-assembled diacetylene molecular wire polymerization on an insulating hexagonal boron nitride (0001) surface. Nanotechnology, 2016, 27, 395303.	1.9	20
23	Facile fabrication of silk protein sericin-mediated hierarchical hydroxyapatite-based bio-hybrid architectures: excellent adsorption of toxic heavy metals and hazardous dye from wastewater. RSC Advances, 2016, 6, 86607-86616.	4.0	42
24	Nanoarchitectonics. Japanese Journal of Applied Physics, 2016, 55, 1102A6.	1.2	66
25	Self-assembling diacetylene molecules on atomically flat insulators. Physical Chemistry Chemical Physics, 2016, 18, 31600-31605.	2.0	8
26	Humidity effects on the redox reactions and ionic transport in a Cu/Ta2O5/Pt atomic switch structure. Japanese Journal of Applied Physics, 2016, 55, 06GJ09.	1.2	55
27	Nanoarchitectonic atomic switch networks for unconventional computing. Japanese Journal of Applied Physics, 2016, 55, 1102B2.	1.2	62
28	Composition of thin Ta2O5 films deposited by different methods and the effect of humidity on their resistive switching behavior. Japanese Journal of Applied Physics, 2016, 55, 06GG08.	1.2	20
29	Identification and roles of nonstoichiometric oxygen in amorphous Ta2O5 thin films deposited by electron beam and sputtering processes. Applied Surface Science, 2016, 385, 426-435.	5.1	42
30	Mechanism for Conducting Filament Growth in Self-Assembled Polymer Thin Films for Redox-Based Atomic Switches. Advanced Materials, 2016, 28, 640-648.	17.5	151
31	In Situ Tuning of Magnetization and Magnetoresistance in Fe3O4 Thin Film Achieved with All-Solid-State Redox Device. ACS Nano, 2016, 10, 1655-1661.	11.5	91
32	Controlled Fabrication of Silk Protein Sericin Mediated Hierarchical Hybrid Flowers and Their Excellent Adsorption Capability of Heavy Metal Ions of Pb(II), Cd(II) and Hg(II). ACS Applied Materials & Interfaces, 2016, 8, 2380-2392.	5.5	82
33	Redox Reactions at Cu,Ag/Ta2O5 Interfaces and the Effects of Ta2O5 Film Density on the Forming Process in Atomic Switch Structures. Advanced Functional Materials, 2015, 25, 6374-6381.	11.9	170
34	I'm with Rohrer-Sensei Even Now. E-Journal of Surface Science and Nanotechnology, 2015, 13, 263-264.	0.4	0
35	Ultra-Low Voltage and Ultra-Low Power Consumption Nonvolatile Operation of a Three-Terminal Atomic Switch. Advanced Materials, 2015, 27, 6029-6033.	17.5	18
36	Infrared Aluminum Metamaterial Perfect Absorbers for Plasmon-Enhanced Infrared Spectroscopy. Advanced Functional Materials, 2015, 25, 6637-6643.	11.9	152

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37	Nanoarchitectonics: a new materials horizon for nanotechnology. Materials Horizons, 2015, 2, 406-413.	8.5	303
38	Moiré Nanosphere Lithography. ACS Nano, 2015, 9, 6031-6040.	11.5	104
39	Plasmon-mediated photocatalytic activity of wet-chemically prepared ZnO nanowire arrays. Physical Chemistry Chemical Physics, 2015, 17, 7395-7403.	2.0	33
40	Dynamic moderation of an electric field using a SiO2 switching layer in TaOx -based ReRAM. Physica Status Solidi - Rapid Research Letters, 2015, 9, 166-170.	1.3	9
41	In Situ and Nonvolatile Photoluminescence Tuning and Nanodomain Writing Demonstrated by All-Solid-State Devices Based on Graphene Oxide. ACS Nano, 2015, 9, 2102-2110.	11.5	38
42	Tunable morphology from 2D to 3D in the formation of hierarchical architectures from a self-assembling dipeptide: thermal-induced morphological transition to 1D nanostructures. Journal of Materials Science, 2015, 50, 3139-3148.	2.8	8
43	Effect of Ionic Conductivity on Response Speed of SrTiO3-Based All-Solid-State Electric-Double-Layer Transistor. ACS Applied Materials & Interfaces, 2015, 7, 12254-12260.	5.5	40
44	Nanosecond Fast Switching Processes Observed in Gapless-Type, Ta2O5–Based Atomic Switches. Materials Research Society Symposia Proceedings, 2015, 1729, 35-40.	0.1	3
45	Position detection and observation of a conducting filament hidden under a top electrode in a Ta2O5-based atomic switch. Nanotechnology, 2015, 26, 145702.	1.9	21
46	Effects of temperature and ambient pressure on the resistive switching behaviour of polymer-based atomic switches. Journal of Materials Chemistry C, 2015, 3, 5715-5720.	3.6	43
47	Nanoarchitectonics + future leaders = bright success in materials science and technology. Science and Technology of Advanced Materials, 2015, 16, 010302.	4.0	3
48	Ultrahigh-Gain Single SnO2 Microrod Photoconductor on Flexible Substrate with Fast Recovery Speed. Advanced Functional Materials, 2015, 25, 3157-3163.	11.9	106
49	Modulation of superconducting critical temperature in niobium film by using all-solid-state electric-double-layer transistor. Applied Physics Letters, 2015, 107, .	2.3	29
50	Micro x-ray photoemission and Raman spectroscopic studies on bandgap tuning of graphene oxide achieved by solid state ionics device. Applied Physics Letters, 2014, 105, 183101.	2.3	26
51	Nanojunction between Fullerene and One-Dimensional Conductive Polymer on Solid Surfaces. ACS Nano, 2014, 8, 12259-12264.	11.5	26
52	Reversible and nonvolatile modulation of electrical resistance in SnO2by external strain. Applied Physics Express, 2014, 7, 031101.	1.6	5
53	Self-organized atomic switch networks. Japanese Journal of Applied Physics, 2014, 53, 01AA02.	1.2	24
54	A new approach to molecular self-assembly through formation of dipeptide-based unique architectures by artificial supersaturation. Chemical Communications, 2014, 50, 12556-12559.	2.4	9

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55	In Situ and Non-Volatile Bandgap Tuning of Multilayer Graphene Oxide in an All-Solid-State Electric Double-Layer Transistor. Advanced Materials, 2014, 26, 1087-1091.	17.5	85
56	Benchtop Fabrication of Memristive Atomic Switch Networks. Journal of Nanoscience and Nanotechnology, 2014, 14, 2792-2798.	0.6	7
57	Rohrer Sensei Never Dies, but He is in the Sky. Hyomen Kagaku, 2014, 35, 533-534.	0.1	0
58	Generic Relevance of Counter Charges for Cation-Based Nanoscale Resistive Switching Memories. ACS Nano, 2013, 7, 6396-6402.	11.5	243
59	Morphological Transitions from Dendrites to Nanowires in the Electroless Deposition of Silver. Crystal Growth and Design, 2013, 13, 465-469.	2.4	48
60	Monitoring the Presence of Ionic Mercury in Environmental Water by Plasmon-Enhanced Infrared Spectroscopy. Scientific Reports, 2013, 3, .	2.7	103
61	Ordered Monomolecular Layers as a Template for the Regular Arrangement of Gold Nanoparticles. Langmuir, 2013, 29, 7334-7343.	3.0	9
62	Double-Side-Coated Nanomechanical Membrane-Type Surface Stress Sensor (MSS) for One-Chip–One-Channel Setup. Langmuir, 2013, 29, 7551-7556.	3.0	21
63	A theoretical and experimental study of neuromorphic atomic switch networks for reservoir computing. Nanotechnology, 2013, 24, 384004.	1.9	240
64	Quantized Conductance and Neuromorphic Behavior of a Gapless-Type Ag-Ta2O5 Atomic Switch. Materials Research Society Symposia Proceedings, 2013, 1562, .	0.1	6
65	Nonvolatile three-terminal operation based on oxygen vacancy drift in a Pt/Ta2O5−x/Pt, Pt structure. Applied Physics Letters, 2013, 102, 233508.	2.3	13
66	All-solid-state electric-double-layer transistor based on oxide ion migration in Gd-doped CeO2 on SrTiO3 single crystal. Applied Physics Letters, 2013, 103, .	2.3	57
67	Synaptic plasticity and memory functions achieved in a WO3−x-based nanoionics device by using the principle of atomic switch operation. Nanotechnology, 2013, 24, 384003.	1.9	144
68	Two Dimensional Array of Piezoresistive Nanomechanical Membrane-Type Surface Stress Sensor (MSS) with Improved Sensitivity. Sensors, 2012, 12, 15873-15887.	2.3	81
69	Impacts of Temperature and Moisture on the Resistive Switching Characteristics of a Cu-Ta2O5-Based Atomic Switch. Materials Research Society Symposia Proceedings, 2012, 1430, .	0.1	1
70	Oxygen migration process in the interfaces during bipolar resistance switching behavior of WO3−x-based nanoionics devices. Applied Physics Letters, 2012, 100, .	2.3	47
71	Flexible Polymer Atomic Switches using Ink-Jet Printing Technique. Materials Research Society Symposia Proceedings, 2012, 1430, .	0.1	2
72	Multilayer Silicene Nanoribbons. Nano Letters, 2012, 12, 5500-5503.	6.2	162

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73	On-Demand Nanodevice with Electrical and Neuromorphic Multifunction Realized by Local Ion Migration. ACS Nano, 2012, 6, 9515-9521.	11.5	199
74	Selective Adsorption of Thiol Molecules at Sulfur Vacancies on MoS2(0001), Followed by Vacancy Repair via S–C Dissociation. Journal of Physical Chemistry C, 2012, 116, 22411-22416.	2.3	162
75	Controlling Semiconducting and Insulating States of SnO2 Reversibly by Stress and Voltage. ACS Nano, 2012, 6, 7209-7215.	11.5	18
76	Enhancing the Humidity Sensitivity of Ga2O3/SnO2 Core/Shell Microribbon by Applying Mechanical Strain and Its Application as a Flexible Strain Sensor. Small, 2012, 8, 3599-3604.	7.3	36
77	Conductance quantization and synaptic behavior in a Ta2O5-based atomic switch. Nanotechnology, 2012, 23, 435705.	1.9	182
78	One-step fabrication of β-Ga2O3–amorphous-SnO2 core–shell microribbons and their thermally switchable humidity sensing properties. Journal of Materials Chemistry, 2012, 22, 12882.	7.3	39
79	Neuromorphic Atomic Switch Networks. PLoS ONE, 2012, 7, e42772.	1.5	164
80	Size Effect on the Structure and Optical Properties in Nanocrystalline SrTiO₃. E-Journal of Surface Science and Nanotechnology, 2012, 10, 406-410.	0.4	6
81	Atom Movement Controlled Devices: Atomic Switches and Atom Transistor. ECS Meeting Abstracts, 2012, MA2012-02, 2838-2838.	0.0	0
82	Forming nanomaterials as layered functional structures toward materials nanoarchitectonics. NPG Asia Materials, 2012, 4, e17-e17.	6.0	393
83	Atomically controlled electrochemical nucleation at superionic solid electrolyte surfaces. Nature Materials, 2012, 11, 530-535.	23.7	228
84	Controlling the Synaptic Plasticity of a Cu2S Gap-Type Atomic Switch. Advanced Functional Materials, 2012, 22, 3606-3613.	11.9	177
85	Effects of Moisture on the Switching Characteristics of Oxide-Based, Gapless-Type Atomic Switches. Advanced Functional Materials, 2012, 22, 70-77.	11.9	266
86	Atomic Switch: Atom/Ion Movement Controlled Devices for Beyond Von-Neumann Computers. Advanced Materials, 2012, 24, 252-267.	17.5	376
87	Impact of Air on Photo-Assisted Atomic Switch. ECS Meeting Abstracts, 2012, MA2012-02, 2850-2850.	0.0	0
88	Nanoionics Switching Devices: “Atomic Switches”. MRS Bulletin, 2011, 34, 929-934.	3.5	55
89	Sensory and short-term memory formations observed in a Ag2S gap-type atomic switch. Applied Physics Letters, 2011, 99, .	2.3	67
90	Rate-Determining Factors in the Chain Polymerization of Molecules Initiated by Local Single-Molecule Excitation. ACS Nano, 2011, 5, 2779-2786.	11.5	35

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91	Molecular-Scale Size Tuning of Covalently Bound Assembly of C60 Molecules. ACS Nano, 2011, 5, 7830-7837.	11.5	23
92	Chemical Wiring and Soldering toward All-Molecule Electronic Circuitry. Journal of the American Chemical Society, 2011, 133, 8227-8233.	11.7	107
93	Macroscopic Superconducting Current through a Silicon Surface Reconstruction with Indium Adatoms:Si(111)–(7×3)–In. Physical Review Letters, 2011, 107, .	5.8	177
94	Surface-enhanced ATR-IR spectroscopy with interface-grown plasmonic gold-island films near the percolation threshold. Physical Chemistry Chemical Physics, 2011, 13, 4935.	2.0	92
95	Direct Observation of X-ray Induced Atomic Motion Using Scanning Tunneling Microscope Combined with Synchrotron Radiation. Journal of Nanoscience and Nanotechnology, 2011, 11, 2873-2881.	0.6	4
96	Nanoscale Control of Reversible Chemical Reaction Between Fullerene C₆₀ Molecules Using Scanning Tunneling Microscope. Journal of Nanoscience and Nanotechnology, 2011, 11, 2829-2835.	0.6	18
97	Short-term plasticity and long-term potentiation mimicked in single inorganic synapses. Nature Materials, 2011, 10, 591-595.	23.7	1,768
98	Temperature effects on the switching kinetics of a Cu–Ta2O5-based atomic switch. Nanotechnology, 2011, 22, 254013.	1.9	83
99	Memristive operations demonstrated by gap-type atomic switches. Applied Physics A: Materials Science and Processing, 2011, 102, 811-815.	2.1	44
100	A Polymer-Electrolyte-Based Atomic Switch. Advanced Functional Materials, 2011, 21, 93-99.	11.9	137
101	Scanning tunneling microscopy and spectroscopy of electron-irradiated thin films of C60 molecules. Carbon, 2011, 49, 1829-1833.	8.6	17
102	Pinecone-shaped ZnO nanostructures: Growth, optical and gas sensor properties.. Sensors and Actuators B: Chemical, 2011, 157, 98-102.	6.3	40
103	ON-State Reliability of Solid-Electrolyte Switch under Pulsed Alternating Current Stress for Programmable Logic Device. Japanese Journal of Applied Physics, 2011, 50, 074201.	1.2	6
104	A quadruple-scanning-probe force microscope for electrical property measurements of microscopic materials. Nanotechnology, 2011, 22, 285205.	1.9	20
105	Theoretical investigation of kinetics of a Cu2S-based gap-type atomic switch. Applied Physics Letters, 2011, 98, .	2.3	17
106	Switching kinetics of a Cu2S-based gap-type atomic switch. Nanotechnology, 2011, 22, 235201.	1.9	75
107	Atomic switches: atomic-movement-controlled nanodevices for new types of computing. Science and Technology of Advanced Materials, 2011, 12, 013003.	4.0	41
108	Focus on Materials Nanoarchitectonics. Science and Technology of Advanced Materials, 2011, 12, 040301.	4.0	23

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109	ON-State Reliability of Solid-Electrolyte Switch under Pulsed Alternating Current Stress for Programmable Logic Device. Japanese Journal of Applied Physics, 2011, 50, 074201.	1.2	8
110	Nonvolatile Crossbar Switch Using $\hbox{TiO}_{x}/ \hbox{TaSiO}_{y}$ Solid Electrolyte. IEEE Transactions on Electron Devices, 2010, 57, 1987-1995.	2.2	37
111	The Atomic Switch. Proceedings of the IEEE, 2010, 98, 2228-2236.	8.6	65
112	Molecular Scale Control of Unbound and Bound C60 for Topochemical Ultradense Data Storage in an Ultrathin C60 Film. Advanced Materials, 2010, 22, 1622-1625.	17.5	67
113	Learning Abilities Achieved by a Single Solid-State Atomic Switch. Advanced Materials, 2010, 22, 1831-1834.	17.5	289
114	Photoassisted Formation of an Atomic Switch. Small, 2010, 6, 1745-1748.	7.3	34
115	ZnO-Based Ultraviolet Photodetectors. Sensors, 2010, 10, 8604-8634.	2.3	704
116	Electronic States of Sulfur Vacancies Formed on a MoS2 Surface. Japanese Journal of Applied Physics, 2010, 49, 08LB01.	1.2	20
117	Rate-Limiting Processes Determining the Switching Time in a Ag2S Atomic Switch. Journal of Physical Chemistry Letters, 2010, 1, 604-608.	2.9	105
118	Structural characterization of amorphous Ta2O5 and SiO2–Ta2O5 used as solid electrolyte for nonvolatile switches. Applied Physics Letters, 2010, 97, .	2.3	18
119	Giant Improvement of the Performance of ZnO Nanowire Photodetectors by Au Nanoparticles. Journal of Physical Chemistry C, 2010, 114, 19835-19839.	2.3	365
120	Nonvolatile triode switch using electrochemical reaction in copper sulfide. Applied Physics Letters, 2010, 96, .	2.3	28
121	First-Principles Study on Electric and Electronic Properties of P-Introduced Si Monatomic Chains. Journal of Computational and Theoretical Nanoscience, 2009, 6, 2635-2639.	0.1	0
122	Metal Nanowire Formation by Solid-Electrochemical Reaction and Its Device Application. Journal of the Vacuum Society of Japan, 2009, 52, 340-346.	0.1	1
123	Nanoscale elemental identification by synchrotron-radiation-based scanning tunneling microscopy. Surface and Interface Analysis, 2008, 40, 1033-1036.	1.5	13
124	Optically monitored wet-chemical preparation of SEIRA active Au nanostructures. Surface and Interface Analysis, 2008, 40, 1681-1683.	1.5	11
125	Reversibility-Controlled Single Molecular Level Chemical Reaction in a C60 Monolayer via Ionization Induced by Scanning Transmission Microscopy. Small, 2008, 4, 538-541.	7.3	38
126	A solid electrolyte nanometer switch. Electrical Engineering in Japan (English Translation of Denki Gakkai Ronbunshi), 2008, 165, 68-73.	0.2	2

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127	Inelastic scattering in electron transport from a metal tip through a nanoscale metal cluster into a GaAs substrate. Surface Science, 2008, 602, L45-L48.	1.5	2
128	Diffusivity of Cu Ions in Solid Electrolyte and Its Effect on the Performance of Nanometer-Scale Switch. IEEE Transactions on Electron Devices, 2008, 55, 3283-3287.	2.2	123
129	Effect of sulfurization conditions on structural and electrical properties of copper sulfide films. Journal of Applied Physics, 2008, 103, .	1.6	56
130	Atomic force microscopy and theoretical investigation of the lifted-up conformation of polydiacetylene on a graphite substrate. Soft Matter, 2008, 4, 1041.	1.9	38
131	Structural studies of copper sulfide films: effect of ambient atmosphere. Science and Technology of Advanced Materials, 2008, 9, 035011.	4.0	108
132	The excitation of one-dimensional plasmons in Si and Au–Si complex atom wires. Nanotechnology, 2008, 19, 355204.	1.9	11
133	Nanostencil-Fabricated Electrodes for Electron Transport Measurements of Atomically Thin Nanowires in Ultrahigh Vacuum. Japanese Journal of Applied Physics, 2008, 47, 1797.	1.2	11
134	Low resistivity of Pt silicide nanowires measured using double-scanning-probe tunneling microscope. Applied Physics Letters, 2008, 92, .	2.3	15
135	Disappearance of the quasi-one-dimensional plasmon at the metal-insulator phase transition of indium atomic wires. Physical Review B, 2008, 77, .	2.4	27
136	Editorial Nanosensors for Defense and Security. IEEE Sensors Journal, 2008, 8, 641-646.	3.0	1
137	Title is missing!. Journal of the Vacuum Society of Japan, 2008, 51, 433-438.	0.1	0
138	Three-Terminal Nanometer Metal Switches Utilizing Solid Electrolytes. IEEJ Transactions on Electronics, Information and Systems, 2008, 128, 890-895.	0.1	0
139	Precisely Controlled Fabrication of a Highly Sensitive Au Sensor Film for Surface Enhanced Spectroscopy. Japanese Journal of Applied Physics, 2007, 46, L1222.	1.2	8
140	Substrate Dependent Low-Temperature Growth of Thin Ag Films: Study on Si(111)–In Surfaces. Japanese Journal of Applied Physics, 2007, 46, 5975.	1.2	6
141	Electronic transport in Ta2O5 resistive switch. Applied Physics Letters, 2007, 91, .	2.3	228
142	In situ Surface-Enhanced Infrared Absorption Spectroscopy for the Analysis of the Adsorption and Desorption Process of Au Nanoparticles on the SiO2/Si Surface. Langmuir, 2007, 23, 6119-6125.	3.0	52
143	Anomalous phase transition and ionic conductivity of AgI nanowire grown using porous alumina template. Journal of Applied Physics, 2007, 102, .	1.6	26
144	Resistance switching of an individual Ag2S/Ag nanowire heterostructure. Nanotechnology, 2007, 18, 485202.	1.9	97

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145	Chain Polymerization of Diacetylene Compound Multilayer Films on the Topmost Surface Initiated by a Scanning Tunneling Microscope Tip. Langmuir, 2007, 23, 5247-5250.	3.0	43
146	Stable molecular orientations of a C60 dimer in a photoinduced dimer row. Carbon, 2007, 45, 1261-1266.	8.6	10
147	Nanoionics-based resistive switching memories. Nature Materials, 2007, 6, 833-840.	23.7	4,918
148	First-principles study on electronic responses of a C60 molecule to external electric fields. Chemical Physics, 2007, 342, 135-140.	1.8	5
149	Control of local ion transport to create unique functional nanodevices based on ionic conductors. Science and Technology of Advanced Materials, 2007, 8, 536-542.	4.0	34
150	Electrical Conductivity of Low-Dimensional Nanostructures. ECS Meeting Abstracts, 2007, MA2007-02, 1193-1193.	0.0	0
151	Adsorption and Desorption of Au Nanoparticles Monitored by Infrared Spectroscopy. IEEJ Transactions on Electronics, Information and Systems, 2007, 127, 2171-2174.	0.1	0
152	Effect of sulfurization conditions and post-deposition annealing treatment on structural and electrical properties of silver sulfide films. Journal of Applied Physics, 2006, 99, 103501.	1.6	57
153	Formation of Metastable Silver Nanowires of Hexagonal Structure and Their Structural Transformation under Electron Beam Irradiation. Japanese Journal of Applied Physics, 2006, 45, 6046-6048.	1.2	29
154	Construction of Independently Driven Double-Tip Scanning Tunneling Microscope. Journal of the Japan Society for Precision Engineering Contributed Papers, 2006, 72, 862-866.	0.1	0
155	Development of a scanning tunneling microscope forin situexperiments with a synchrotron radiation hard-X-ray microbeam. Journal of Synchrotron Radiation, 2006, 13, 216-220.	1.9	45
156	Control of conduction of iodine-doped poly(3-octylthiophene) thin films by double-tip scanning tunneling microscopy. Chemical Physics Letters, 2006, 419, 250-253.	2.0	2
157	Template synthesis of M/M2S (M=Ag, Cu) hetero-nanowires by electrochemical technique. Solid State Ionics, 2006, 177, 2527-2531.	2.6	17
158	Tunneling-current-induced light emission from individual carbon nanotubes. Surface Science, 2006, 600, L15-L19.	1.5	16
159	Fabrication of nanostructures by selective growth of C60 and Si on Si(111) substrate. Surface Science, 2006, 600, 2810-2816.	1.5	14
160	Scanning Tunneling Microscopy Combined with Hard X-ray Microbeam of High Brilliance from Synchrotron Radiation Source. Japanese Journal of Applied Physics, 2006, 45, 1913-1916.	1.2	8
161	Scanning Tunneling Microscope Study of a Local Electronic State Surrounding Mn Nanoclusters on Graphite. Japanese Journal of Applied Physics, 2006, 45, L469-L471.	1.2	2
162	Polaron Injection into One-Dimensional Polydiacetylene Nanowire. Japanese Journal of Applied Physics, 2006, 45, 2049-2052.	1.2	13

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163	Application of Simple Mechanical Polishing to Fabrication of Nanogap Flat Electrodes. Japanese Journal of Applied Physics, 2006, 45, L145-L147.	1.2	18
164	Effect of Ion Diffusion on Switching Voltage of Solid-Electrolyte Nanometer Switch. Japanese Journal of Applied Physics, 2006, 45, 3666-3668.	1.2	62
165	Switching Property of Atomic Switch Controlled by Solid Electrochemical Reaction. Japanese Journal of Applied Physics, 2006, 45, L364-L366.	1.2	37
166	Tunneling-Current-Induced Light Emission from Copper Phthalocyanine Thin Films. E-Journal of Surface Science and Nanotechnology, 2006, 4, 559-562.	0.4	6
167	Atomic Switch-Nano Device using the Transfer of Atoms(Ions)-. Hyomen Kagaku, 2006, 27, 232-238.	0.1	3
168	Solid Electrolyte Nanometer Switch. IEEJ Transactions on Electronics, Information and Systems, 2006, 126, 714-719.	0.1	0
169	Sum-frequency generation of the symmetric CH3-stretching vibration in organized molecular ultrathin films: ultrafast coupling interaction effect. Colloids and Surfaces A: Physicochemical and Engineering Aspects, 2005, 257-258, 357-362.	4.2	5
170	Significant increase in conductivity of polydiacetylene thin film induced by iodine doping. Surface Science, 2005, 591, L273-L279.	1.5	39
171	Structural Study of Initial Growth of Nickel on Yttria-Stabilized Zirconia by Coaxial Impact-Collision Ion Scattering Spectroscopy. Japanese Journal of Applied Physics, 2005, 44, 2630-2633.	1.2	0
172	Ionic-Electronic Conductor Nanostructures: Template-Confined Growth and Nonlinear Electrical Transport. Small, 2005, 1, 971-975.	7.3	63
173	Structure of Atomically Smoothed LiNbO3(0001) Surface. Japanese Journal of Applied Physics, 2004, 43, 2057-2060.	1.2	20
174	Epitaxial growth of WOxnanorod array on W(001). Science and Technology of Advanced Materials, 2004, 5, 647-649.	4.0	23
175	Fabrication and electron-beam-induced polymerization of C60 nanoribbon. Thin Solid Films, 2004, 464-465, 327-330.	1.6	28
176	The electron transport properties of photo- and electron-beam-irradiated C60 films. Journal of Physics and Chemistry of Solids, 2004, 65, 343-348.	4.2	38
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